

E Series Power MOSFET with Fast Body Diode

PRODUCT SUMMARY	
V_{DS} (V) at T_J max.	700
$R_{DS(on)}$ typ. at 25 °C (Ω)	$V_{GS} = 10$ V 0.041
Q_g max. (nC)	371
Q_{gs} (nC)	65
Q_{gd} (nC)	93
Configuration	Single

FEATURES

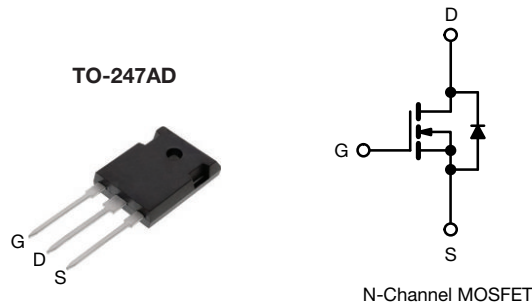
- Fast body diode MOSFET using E series technology
- Reduced t_{rr} , Q_{rr} , and I_{RRM}
- Low figure-of-merit (FOM) $R_{on} \times Q_g$
- Low input capacitance (C_{iss})
- Low switching losses due to reduced Q_{rr}
- Ultra low gate charge (Q_g)
- Avalanche energy rated (UIS)
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Telecommunications
 - Server and telecom power supplies
- Lighting
 - High-intensity lighting (HID)
 - Light emitting diodes (LEDs)
- Consumer and computing
 - ATX power supplies
- Industrial
 - Welding
 - Battery chargers
- Renewable energy
 - Solar (PV inverters)
- Switching mode power supplies (SMPS)
 - Applications using the following topologies
 - LLC
 - Phase shifted bridge (ZVS)
 - 3-level inverter
 - AC/DC bridge



ORDERING INFORMATION	
Package	TO-247AD
Lead (Pb)-Free and Halogen-Free	SiHW61N65EF-GE3


ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C, unless otherwise noted)				
PARAMETER	SYMBOL	LIMIT	UNIT	
Drain-Source Voltage	V_{DS}	650	V	
Gate-Source Voltage	V_{GS}	± 30		
Continuous Drain Current ($T_J = 150$ °C)	V_{GS} at 10 V	$T_C = 25$ °C	64	A
		$T_C = 100$ °C	41	
Pulsed Drain Current ^a	I_{DM}	199		
Linear Derating Factor		4.2	W/°C	
Single Pulse Avalanche Energy ^b	E_{AS}	1142	mJ	
Maximum Power Dissipation	P_D	520	W	
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	°C	
Drain-Source Voltage Slope	dV/dt	70	V/ns	
Reverse Diode dV/dt ^d				50
Soldering Recommendations (Peak temperature) ^c	For 10 s	300	°C	

Notes

- Repetitive rating; pulse width limited by maximum junction temperature.
- $V_{DD} = 140$ V, starting $T_J = 25$ °C, $L = 28.2$ mH, $R_g = 25$ Ω , $I_{AS} = 9$ A.
- 1.6 mm from case.
- $I_{SD} \leq I_D$, $dI/dt = 500$ A/ μ s, starting $T_J = 25$ °C.



THERMAL RESISTANCE RATINGS				
PARAMETER	SYMBOL	TYP.	MAX.	UNIT
Maximum Junction-to-Ambient	R_{thJA}	-	40	°C/W
Maximum Junction-to-Case (Drain)	R_{thJC}	-	0.24	

SPECIFICATIONS ($T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = 250\text{ }\mu\text{A}$	650	-	-	V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	Reference to $25\text{ }^\circ\text{C}, I_D = 10\text{ mA}$	-	0.81	-	V/°C
Gate-Source Threshold Voltage (N)	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	2.0	-	4.0	V
Gate-Source Leakage	I_{GSS}	$V_{GS} = \pm 20\text{ V}$	-	-	± 100	nA
		$V_{GS} = \pm 30\text{ V}$	-	-	± 1	μA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}$	-	-	1	μA
		$V_{DS} = 520\text{ V}, V_{GS} = 0\text{ V}, T_J = 125\text{ }^\circ\text{C}$	-	-	500	
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS} = 10\text{ V}, I_D = 30.5\text{ A}$	-	0.041	0.047	Ω
Forward Transconductance	g_{fs}	$V_{DS} = 30\text{ V}, I_D = 30.5\text{ A}$	-	23	-	S
Dynamic						
Input Capacitance	C_{iss}	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	7407	-	pF
Output Capacitance	C_{oss}		-	351	-	
Reverse Transfer Capacitance	C_{rss}		-	3	-	
Effective Output Capacitance, Energy Related ^a	$C_{o(er)}$	$V_{DS} = 0\text{ V to } 520\text{ V}, V_{GS} = 0\text{ V}$	-	233	-	pF
Effective Output Capacitance, Time Related ^b	$C_{o(tr)}$		-	939	-	
Total Gate Charge	Q_g	$V_{GS} = 10\text{ V}, I_D = 30.5\text{ A}, V_{DS} = 520\text{ V}$	-	247	371	nC
Gate-Source Charge	Q_{gs}		-	65	-	
Gate-Drain Charge	Q_{gd}		-	93	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = 520\text{ V}, I_D = 30.5\text{ A}, V_{GS} = 10\text{ V}, R_g = 9.1\text{ }\Omega$	-	59	89	ns
Rise Time	t_r		-	107	161	
Turn-Off Delay Time	$t_{d(off)}$		-	217	326	
Fall Time	t_f		-	133	200	
Gate Input Resistance	R_g		$f = 1\text{ MHz}, \text{ open drain}$	0.5	1	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	MOSFET symbol showing the integral reverse p - n junction diode 	-	-	64	A
Pulsed Diode Forward Current	I_{SM}		-	-	199	
Diode Forward Voltage	V_{SD}	$T_J = 25\text{ }^\circ\text{C}, I_S = 30.5\text{ A}, V_{GS} = 0\text{ V}$	-	0.9	1.2	V
Reverse Recovery Time	t_{rr}	$T_J = 25\text{ }^\circ\text{C}, I_F = I_S = 30.5\text{ A}, di/dt = 100\text{ A}/\mu\text{s}, V_R = 400\text{ V}$	-	212	474	ns
Reverse Recovery Charge	Q_{rr}		-	2.1	3.8	μC
Reverse Recovery Current	I_{RRM}		-	18	-	A

Notes

- a. $C_{oss(er)}$ is a fixed capacitance that gives the same energy as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .
- b. $C_{oss(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 % to 80 % V_{DSS} .

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

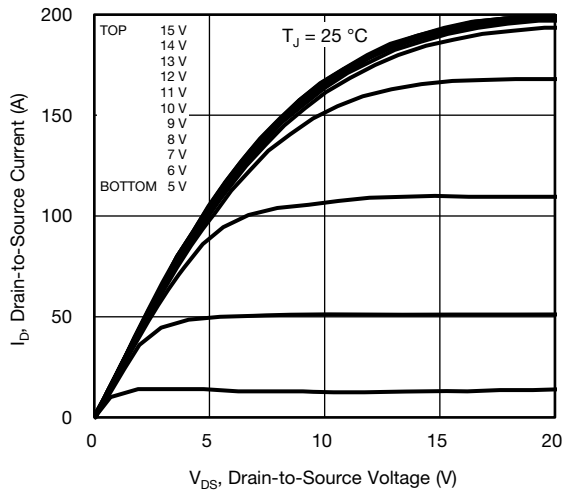


Fig. 1 - Typical Output Characteristics

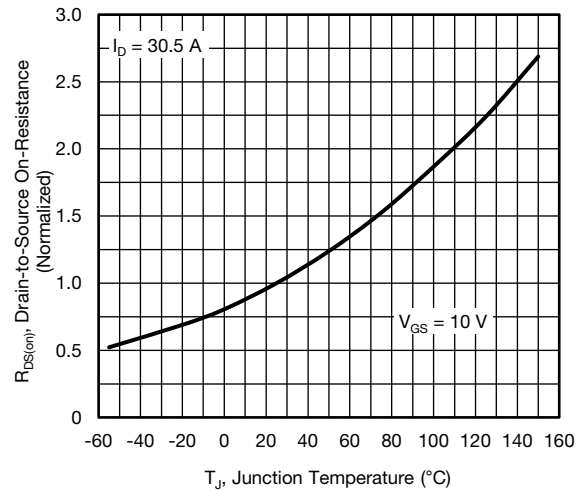


Fig. 4 - Normalized On-Resistance vs. Temperature

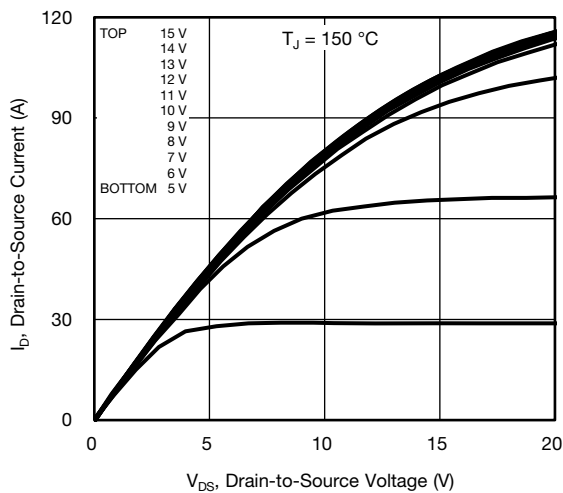


Fig. 2 - Typical Output Characteristics

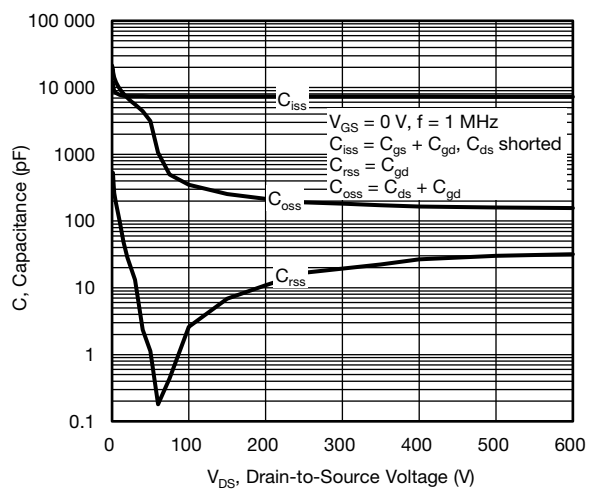


Fig. 5 - Typical Capacitance vs. Drain-to-Source Voltage

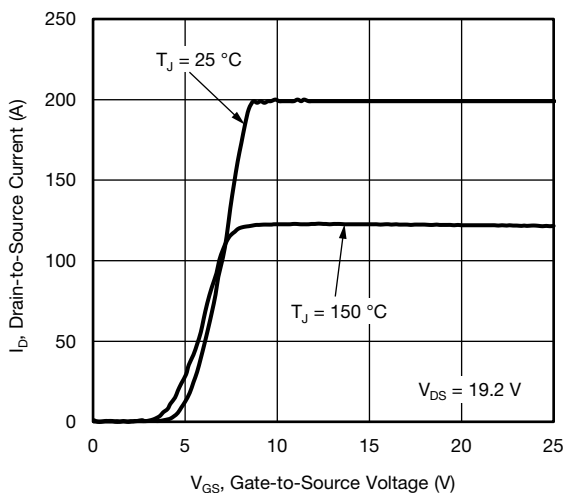


Fig. 3 - Typical Transfer Characteristics

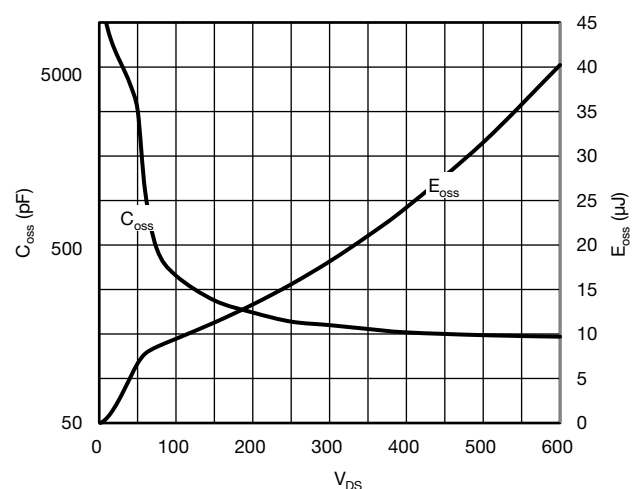


Fig. 6 - C_{oss} and E_{oss} vs. V_{DS}

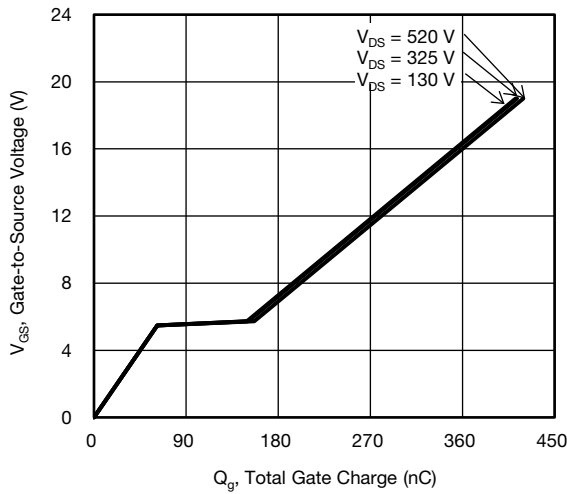


Fig. 7 - Typical Gate Charge vs. Gate-to-Source Voltage

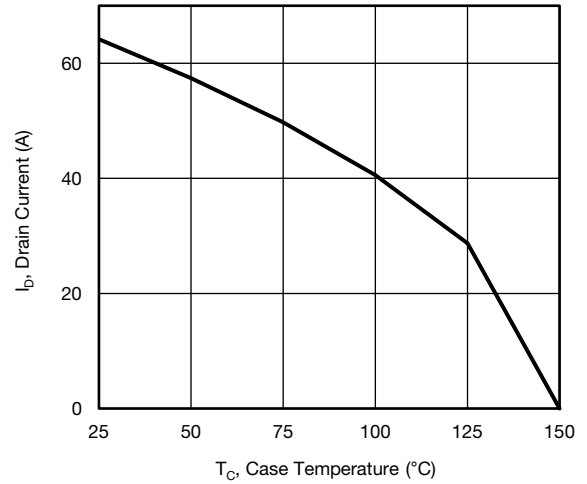


Fig. 10 - Maximum Drain Current vs. Case Temperature

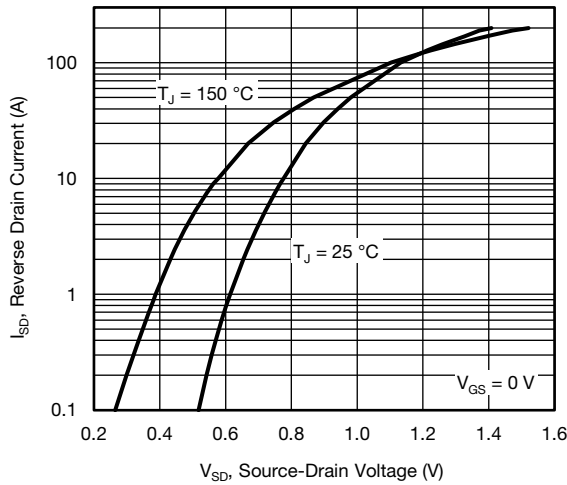


Fig. 8 - Typical Source-Drain Diode Forward Voltage

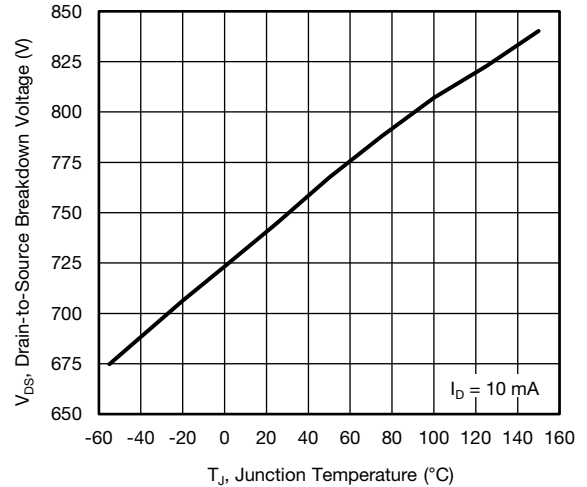


Fig. 11 - Temperature vs. Drain-to-Source Voltage

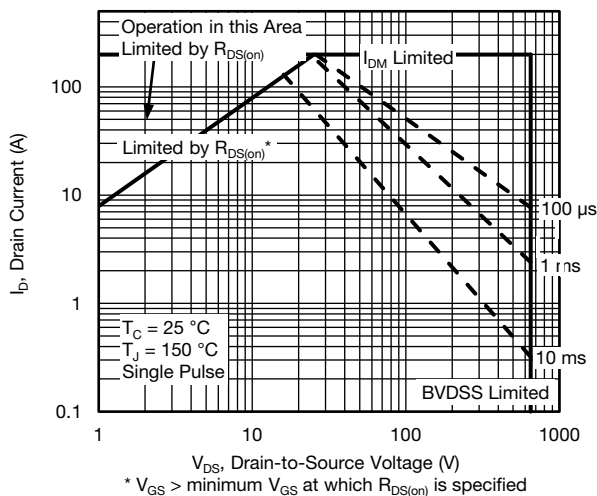


Fig. 9 - Maximum Safe Operating Area

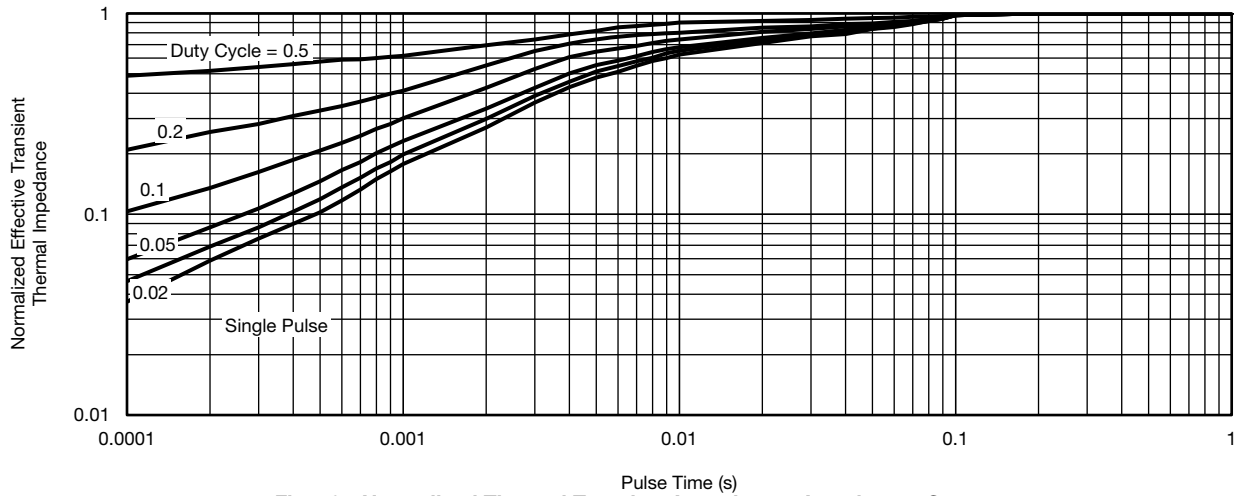


Fig. 12 - Normalized Thermal Transient Impedance, Junction-to-Case

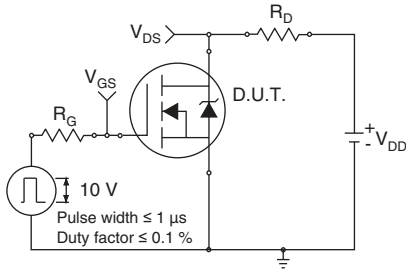


Fig. 13 - Switching Time Test Circuit

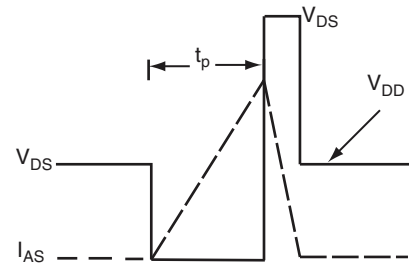


Fig. 16 - Unclamped Inductive Waveforms

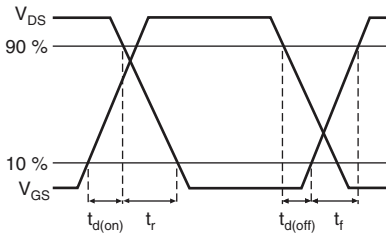


Fig. 14 - Switching Time Waveforms

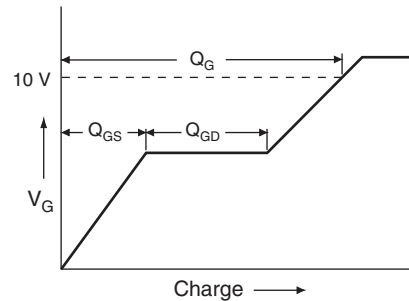


Fig. 17 - Basic Gate Charge Waveform

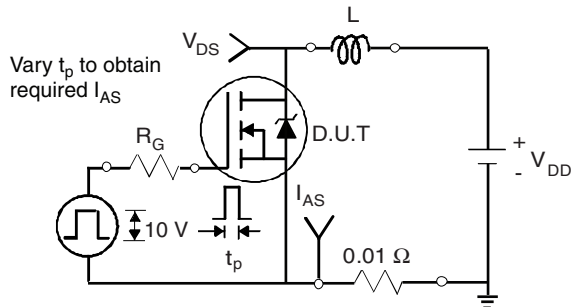


Fig. 15 - Unclamped Inductive Test Circuit

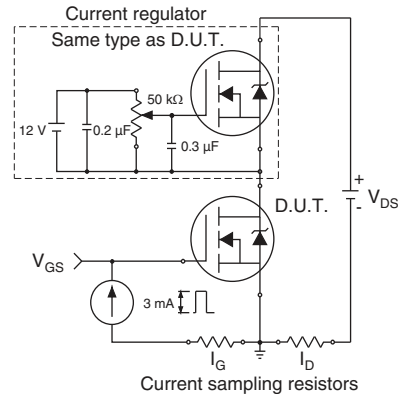
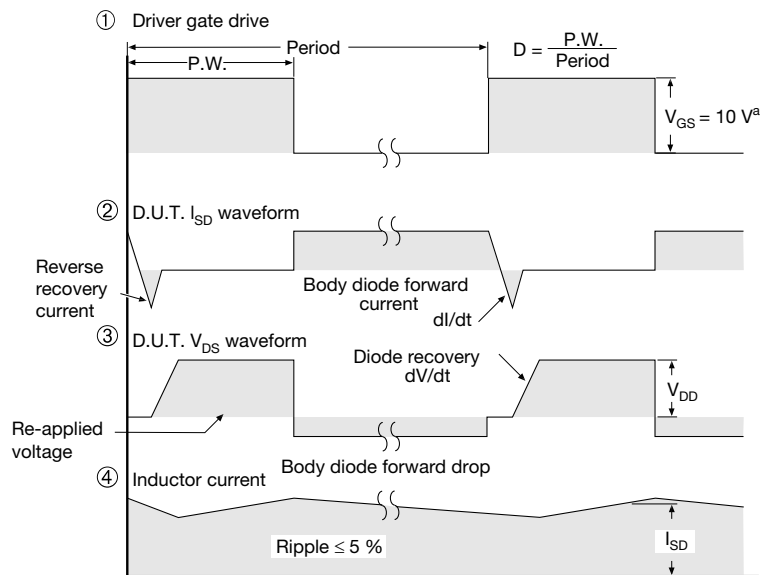


Fig. 18 - Gate Charge Test Circuit

Peak Diode Recovery dV/dt Test Circuit



Note

a. $V_{GS} = 5 V$ for logic level devices

Fig. 19 - For N-Channel

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